Supporting Information

Wet-etching Fabrication of Flexible and Transparent Silicon Frameworks for Imperceptible Wearable Electronics

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Supplementary Figures

**Figure S1.** Photographs of stainless-steel fixtures with a silicon wafer fixed in the middle. (a) A top-view photograph. (b) A side-view photograph.

**Figure S2.** Photographs of a single-thinned silicon wafer. (a) The thinned side. (b) The protected side.
Figure S3. SEM images of sc-SiFs obtained by reactive ion etching (RIE) and wet etching. (a) Sidewalls of sc-SiFs obtained by RIE are rough. (b) Sidewalls of sc-SiFs obtained by wet etching are smooth.

Figure S4. The images of bubbling along the fixture edge in the alkali etching process.
Figure S5. Single-sided thinning of a 4-inch silicon wafer. (a) The 4-inch silicon wafer clamped with large SS fixtures. (b) Photograph of the 4-inch silicon wafer after single-side thinning.

Figure S6. The relative change in resistance of the sc-SiFs sensor under different pressures.